

isc Silicon NPN Power Transistor

BD329

DESCRIPTION

- DC Current Gain-
: $h_{FE} = 85\sim 375(\text{Min}) @ I_C = 0.5A$
- Collector-Emitter Sustaining Voltage -
: $V_{CEO(SUS)} = 20V(\text{Min})$
- Complement to type BD330

APPLICATIONS

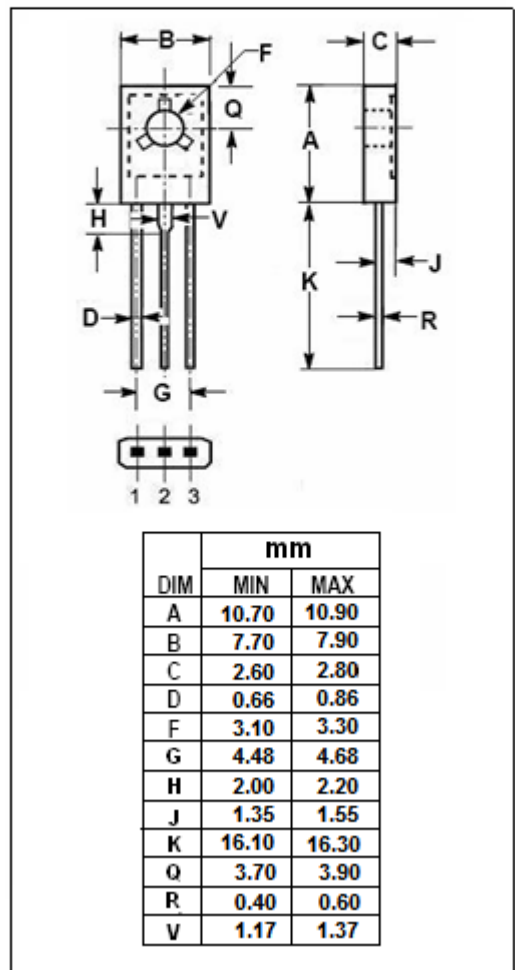
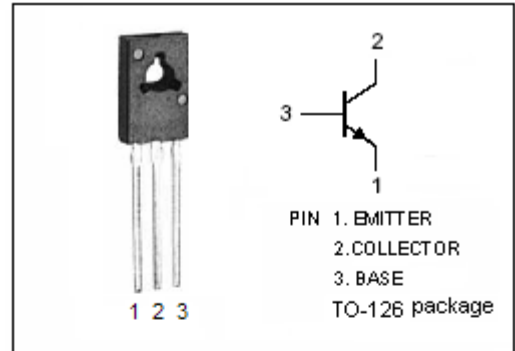
- Especially for battery equipped applications.

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	32	V
V_{CEO}	Collector-Emitter Voltage	20	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	3	A
I_{BM}	Base Current-Peak	1	A
P_C	Collector Power Dissipation @ $T_C=25^\circ\text{C}$	15	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-65~150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	7	$^\circ\text{C/W}$
$R_{th\ j-a}$	Thermal Resistance, Junction to Ambient	100	$^\circ\text{C/W}$



isc Silicon NPN Power Transistor**BD329****ELECTRICAL CHARACTERISTICS** $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	$I_C=30\text{mA}; I_B=0$	20			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=2\text{A}; I_B=0.2\text{A}$			0.5	V
$V_{BE(on)-1}$	Base-Emitter On Voltage	$I_C=5\text{mA}; V_{CE}=10\text{V}$		0.6		V
$V_{BE(on)-2}$	Base-Emitter On Voltage	$I_C=2\text{A}; V_{CE}=1\text{V}$			1.2	V
I_{CBO}	Collector Cutoff Current	$V_{CB}=32\text{V}; I_E=0$ $V_{CB}=32\text{V}; I_E=0, T_C=150^{\circ}\text{C}$			0.1 10	μA
I_{EBO}	Emitter Cutoff Current	$V_{EB}=5\text{V}; I_C=0$			0.1	μA
h_{FE-1}	DC Current Gain	$I_C=5\text{mA}; V_{CE}=10\text{V}$	50			
h_{FE-2}	DC Current Gain	$I_C=0.5\text{A}; V_{CE}=1\text{V}$	85		375	
h_{FE-3}	DC Current Gain	$I_C=2\text{A}; V_{CE}=1\text{V}$	40			
f_T	Current-Gain—Bandwidth Product	$I_C=50\text{mA}; V_{CE}=5\text{V}; f_{test}=100\text{MHz}$		130		MHz